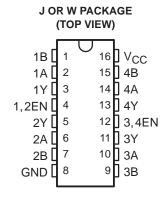
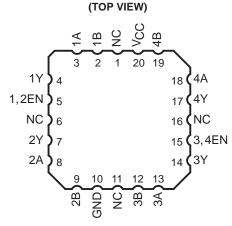
- Meets EIA Standards RS-422-A, RS-423-A, RS-485, and CCITT V.11
- **Designed to Operate With Pulse Durations** as Short as 20 ns
- **Designed for Multipoint Transmission on Long Bus Lines in Noisy Environments**
- Input Sensitivity . . . ±200 mV
- Low-Power Consumption . . . 20 mA Max
- **Open-Circuit Fail-Safe Design**
- Common-Mode Input Voltage Range of -7 V to 12 V

description

The SN55LBC175 is a monolithic quadruple differential line receiver with 3-state outputs and is designed to meet the requirements of the EIA Standards RS-422-A, RS-423-A, RS-485, and CCITT V.11. This device is optimized for balanced multipoint bus transmission at data rates up to and exceeding 10 million bits per second. The receivers are enabled in pairs with an active-high enable input. Each differential receiver input features high impedance, hysteresis for increased noise immunity, and sensitivity of ±200 mV over a common-mode input voltage range of 12 V to -7 V. Fail-safe design ensures that if the inputs are open circuited, the outputs are always high. This device is designed using the Texas Instruments proprietary LinBiCMOS™ technology allowing low power consumption, high switching speeds, and robustness.





FK PACKAGE

NC - No internal connection

This device offers optimum performance when used with the SN55LBC174 quadruple line driver. The SN55LBC175 is available in the 16-pin CDIP (J) package, a 16-pin CPAK (W) package, or a 20-pin LCCC (FK) package.

The SN55LBC175 is characterized over the military temperature range of -55°C to 125°C.

FUNCTION TABLE (each receiver)

DIFFERENTIAL INPUTS A-B	ENABLE	OUTPUT Y
V _{ID} ≥ 0.2 V	Н	Н
$-0.2 \text{ V} < \text{V}_{\text{ID}} < 0.2 \text{ V}$	Н	?
$V_{ID} \le -0.2 V$	Н	L
X	L	Z
Open circuit	Н	Н

H = high level, L = low level, X = irrelevant, Z = high impedance (off), ? = indeterminate



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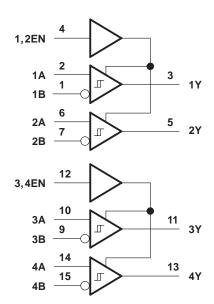


logic symbol†

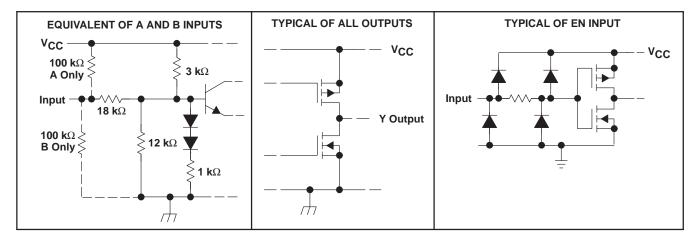
ΕN 1,2EN _ D 3 1A 1Y 1B 6 2A 2Y 2B 3,4EN ΕN 10 ⅎ 11 3A 3Y 9 3B 14 4A 13 15 4B

Pin numbers shown are for the J or W package.

logic diagram (positive logic)



schematics of inputs and outputs



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC} (see Note 1)	$-0.3\ V$ to 7 V
Input voltage, A or B inputs, V _I	±25 V
Differential input voltage, V _{ID} (see Note 2)	±25 V
Data and control voltage range	0.3 V to 7 V
Continuous total dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A	–55°C to 125°C
Storage temperature range, T _{Stq}	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to GND.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{$A$}} \leq 25^{\circ}\mbox{$C$}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 125°C POWER RATING	
FK	1375 mW	11.0 mW/°C	275 mW	
J	1375 mW	11.0 mW/°C	275 mW	
W	1000 mW	8.0 mW/°C	200 mW	

recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}		4.75	5	5.25	V
Common-mode input voltage, V _{IC}	Common-mode input voltage, V _{IC}			12	V
Differential input voltage, V _{ID}				±6	V
High-level input voltage, VIH	EN inputo	2			V
Low-level input voltage, V _{IL}	EN inputs			0.8	V
High-level output current, IOH				-8	mA
Low-level output current, IOL				16	mA
Operating free-air temperature, T _A		-55		125	°C



^{2.} Differential input voltage is measured at the noninverting input with respect to the corresponding inverting input.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

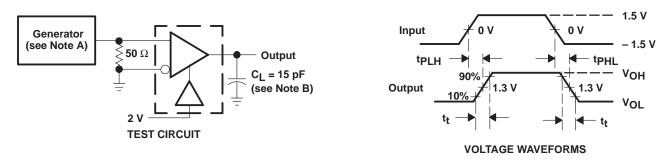
PARAMETER		TEST CONDITIONS			MIN	TYP [†]	MAX	UNIT	
V _{IT+}	Positive-going input thresho	ld voltage	$I_O = -8 \text{ mA}$				0.2	V	
VIT-	Negative-going input thresh	old voltage	I _O =16 mA			-0.2			V
V _{hys}	Hysteresis voltage (V _{IT+} -	V _{IT} _)					45		mV
٧IK	Enable input clamp voltage		$I_{I} = -18 \text{ mA}$				-0.9	-1.5	V
Vон	High-level output voltage		$V_{ID} = 200 \text{ mV},$	I _{OH} = -8 m/	4	3.5	4.5		V
\/a.	Low-level output voltage		$V_{ID} = -200 \text{ mV},$	I _{OL} = 16 mA			0.3	0.5	V
VOL	Low-level output voltage		$V_{ID} = -200 \text{ mV},$	I _{OL} = 16 mA	,T _A = 125°C			0.7	v
loz	High-impedance-state output	ut current	$V_O = 0 V \text{ to } V_{CC}$					±20	μΑ
			V _{IH} = 12 V,	$V_{CC} = 5 V$,	Other inputs at 0 V		0.7	1	
l	Bus input current	A or B	V _{IH} = 12 V,	$V_{CC} = 0 V$	Other inputs at 0 V		0.8	1	mA
'1	bus input current	inputs	$V_{IH} = -7 V$,	$V_{CC} = 5 V$,	Other inputs at 0 V		-0.5	-0.8	IIIA
			$V_{IH} = -7 V$,	$V_{CC} = 0 V$	Other inputs at 0 V		-0.4	-0.8	
lн	High-level enable input curr	ent	V _{IH} = 5 V					±20	μΑ
I _{IL}	Low-level enable input curre	ent	V _{IL} = 0 V					-20	μΑ
los	Short-circuit output current		V _O = 0			·	-80	-120	mA
loo	Supply current		Outputs enabled,	$I_{O} = 0$,	V _{ID} = 5 V		11	20	mA
I'CC	ICC Supply current		Outputs disabled				0.9	1.4	IIIA

 $[\]dagger$ All typical values are at V_{CC} = 5 V and T_A = 25°C.

switching characteristics, V_{CC} = 5 V, C_L = 15 pF

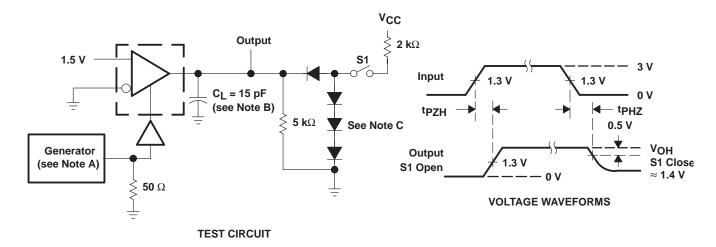
	PARAMETER	TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
t	Propagation delay time, high- to low-level output	$V_{ID} = -1.5 \text{ V to } 1.5 \text{ V},$	25°C	11	22	30	ns
tPHL	Propagation delay time, high- to low-level output	See Figure 1	-55°C to 125°C			35	
	Propagation delay time, low- to high-level output	$V_{ID} = -1.5 \text{ V to } 1.5 \text{ V},$	25°C	11	22	30	ns
^t PLH	Propagation delay time, low- to high-level output	See Figure 1	-55°C to 125°C			35	
	Output anable time to high level	Soo Figure 2	25°C		17	40	no
^t PZH	Output enable time to high level	See Figure 2	-55°C to 125°C			45	ns
4	Output analys time to low lovel	Can Figure 2	25°C		18	30	
tPZL	Output enable time to low level	See Figure 3	-55°C to 125°C			35	ns
	Output disable time from high level	San Figure 2	25°C		30	40	20
^t PHZ	Output disable time from high level	See Figure 2	-55°C to 125°C			55	ns
4	Output disable time from law lavel	Can Figure 2	25°C		23	30	
^t PLZ	Output disable time from low level	See Figure 3	-55°C to 125°C			45	ns
		25°C		4	6		
tsk(p)	Pulse skew (tpHL - tpLH)	See Figure 1	-55°C to 125°C			7	ns
4 Transition time	Transition time	See Figure 1	25°C		3	10	20
t _t	Transition time		-55°C to 125°C			16	ns

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle \leq 50%, $t_{\text{f}} \leq$ 6 ns, $t_{\text{f}} \leq$ 7 ns, $t_{\text{f}} \leq$ 8 ns, $t_{\text{f}} \leq$ 9 ns, t
 - B. C_I includes probe and jig capacitance.

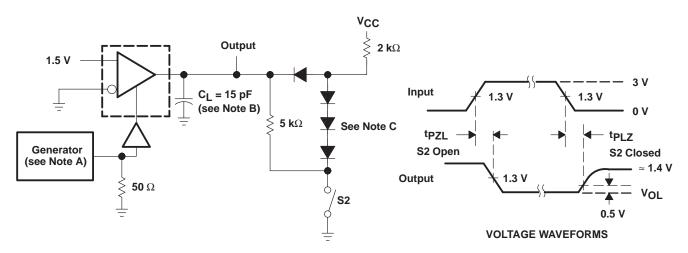
Figure 1. t_{PLH} and t_{PHL} Test Circuit and Voltage Waveforms



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle \leq 50%, $t_f \leq$ 6 ns, $t_f \leq$ 7 ns, $t_f \leq$ 8 ns, $t_f \leq$ 9 ns, $t_$
 - B. C_L includes probe and jig capacitance.
 - C. All diodes are 1N916 or equivalent.

Figure 2. t_{PHZ} and t_{PZH} Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION

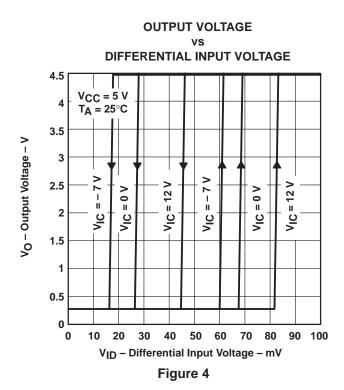


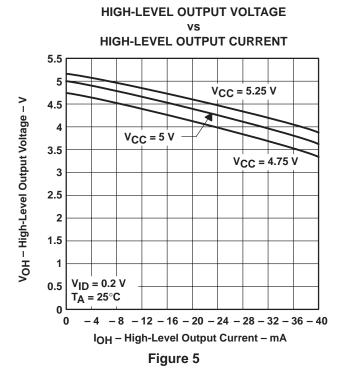
TEST CIRCUIT

- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle \leq 50%, $t_{\Gamma} \leq$ 6 ns, $t_{\Gamma} \leq$ 7 ns, $t_{\Gamma} \leq$ 8 ns,
 - B. C_L includes probe and jig capacitance.
 - C. All diodes are 1N916 or equivalent.

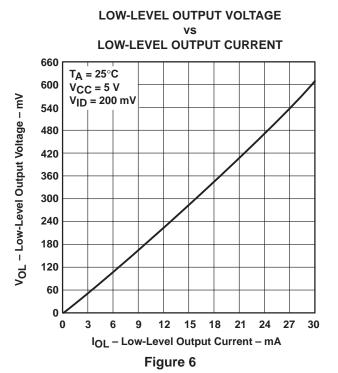
Figure 3. tpzL and tpLZ Test Circuit and Voltage Waveforms

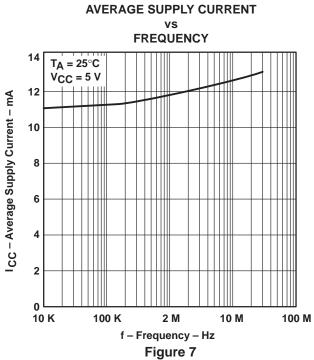
TYPICAL CHARACTERISTICS



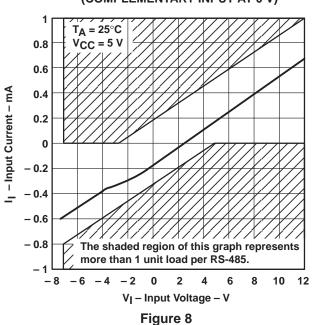


TYPICAL CHARACTERISTICS

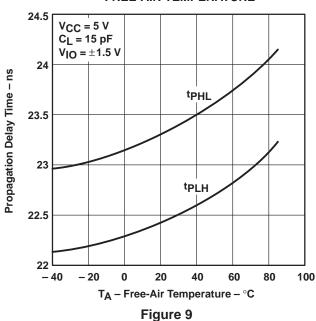




BUS
INPUT CURRENT
vs
INPUT VOLTAGE
(COMPLEMENTARY INPUT AT 0 V)



PROPAGATION DELAY TIME vs FREE-AIR TEMPERATURE



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